

EE236: Experiment No. 8

P-channel MOSFET I-V Characteristics

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1 Overview of the experiment

1.1 Aim of the experiment

- Measuring output and transfer characteristics of a P-channel enhancement type MOSFET (also called PMOS).
- Investigating the effect of body bias on the characteristics of the PMOS.

1.2 Methods

- Obtaining the values of V_t and g_m using the plot of linear Transfer Characteristics of the mosfet.

$$g_m = \left. \frac{d(ID)}{d(VSG)} \right|_{atconstVSD} \quad (1)$$

- finding the output resistance r_o using the slope of the plot of ID vs V_{sd} for drain characteristics.

$$r_o = \left. \frac{d(VSD)}{d(ID)} \right|_{atconstVSG} \quad (2)$$

- finding the body effect co-efficient by plotting V_T vs V_{sb} by changing the V_{sb} .
- $V_T = V_{T_o} + \gamma(\sqrt{si(s)} - \sqrt{si(s)})$

2 Design

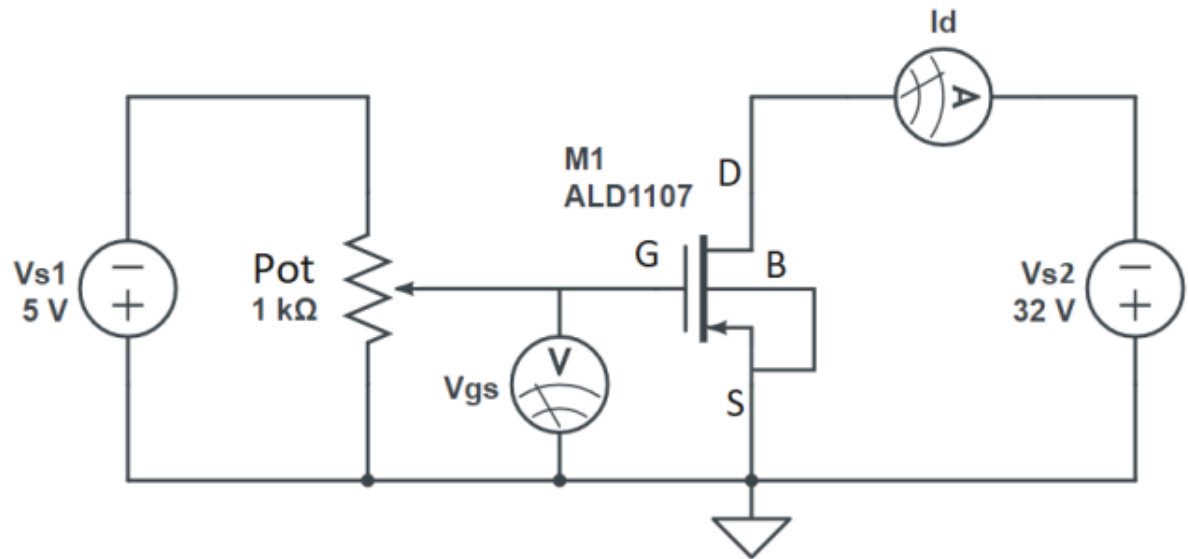


Figure 1: Circuit for linear transfer characteristics and drain characteristics

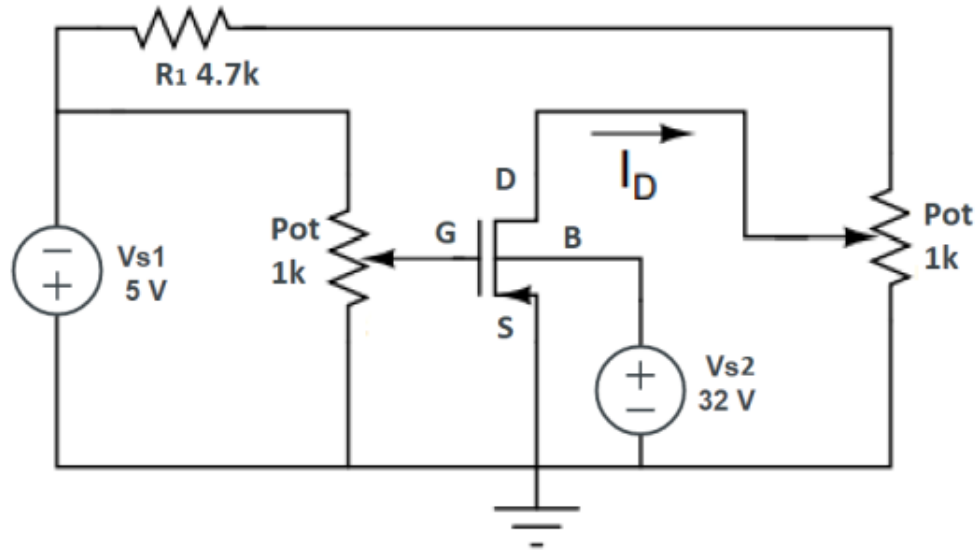


Figure 2: PMOS body effect circuit.

2.1 Experimental results

$g_m = 4/0.15 = 13.33$. $r_0 = 0.5/0.59 = 0.82$. $\gamma = 0.398$.

part(1)

VSD = 5V VSD = .2V

ID	VSG	ID	VSG
0	0.07	0	0.2
0	0.58	0	0.799
0	0.9	0.072	1.89
0.015	1	0.082	2.07
0.038	1.19	0.095	2.3
0.045	1.23	0.106	2.54
0.063	1.34	0.119	2.82
0.121	1.59	0.128	3
0.157	1.72	0.136	3.23
0.215	1.91	0.152	3.61
0.293	2.13	0.165	4.14
0.319	2.19	0.178	4.38

0.352	2.28	0.184	4.6
0.4	2.4	0.191	4.81
0.638	2.91	0.193	4.88
0.829	3.28	0.196	4.97
0.953	3.5		
1.245	3.99		
1.376	4.19		
1.543	4.45		
1.9	4.97		

part(2)

Vsd	Id1	Id2	Id3
0.02	0.005		
0.27	0.051		
0.48	0.073		
0.59	0.079		
0.74	0.083		
0.85	0.085		
1.93	0.092		
2.07	0.093		
3.51	0.099		
3.78	0.1		
4	0.101		
4.33	0.102		
4.72	0.103		
5.05	0.104		
0.02	0.01		
0.19	0.084		
0.28	0.122		
0.35	0.146		
0.39	0.162		
0.63	0.24		
0.75	0.273		
0.92	0.311		
1.46	0.383		

2.14 0.406
2.64 0.416
3.08 0.423
3.72 0.432
4.21 0.438
4.45 0.44
5.05 0.447
0.02 0.014
0.19 0.124
0.3 0.185
0.42 0.257
0.53 0.312
0.58 0.342
0.73 0.415
0.96 0.518
1.21 0.618
1.4 0.681
1.9 0.807
2.55 0.883
2.76 0.895
3.07 0.909
3.74 0.932
3.98 0.939
4.63 0.955
4.91 0.961
5.02 0.963

Part(3)

Vsg Vsb = -1
0.01 0
0.95 0
0.984 0.001
1.14 0.005
1.18 0.008
1.25 0.012

1.38	0.019
1.48	0.025
1.56	0.029
1.73	0.04
2.05	0.055
2.2	0.064
2.49	0.077
2.83	0.09
3.13	0.099
3.69	0.115
3.87	0.12
4.47	0.144
4.88	0.159
5	0.165

Vsg	Vsb = -2
0.01	0
0.1	0
1.07	0
1.09	0.001
1.24	0.005
1.34	0.01
1.41	0.014
1.53	0.021
1.67	0.028
1.8	0.034
2.08	0.054

2.22	0.056
2.47	0.066
2.63	0.076
2.84	0.084
3.12	0.093
3.32	0.1
3.51	0.112
3.75	0.119
3.98	0.126
4.14	0.13

4.55 0.14
 4.72 0.144
 5 0.15

Vgs Vsb = -3
 0.01 0
 0.39 0
 1.18 0
 1.195 0.001
 1.26 0.002
 1.39 0.008
 1.47 0.012
 1.67 0.022
 1.85 0.032
 1.99 0.038
 2.19 0.046
 2.51 0.065
 2.76 0.074
 3.2 0.09
 3.39 0.1
 3.67 0.108
 3.97 0.116
 4.18 0.122
 4.51 0.13
 5 0.141

Vsb Vt gamma
 0 0.78
 -1 0.958 0.398020099994962

-2 1.09 0.39800082283055
-3 1.195 0.39339040496137

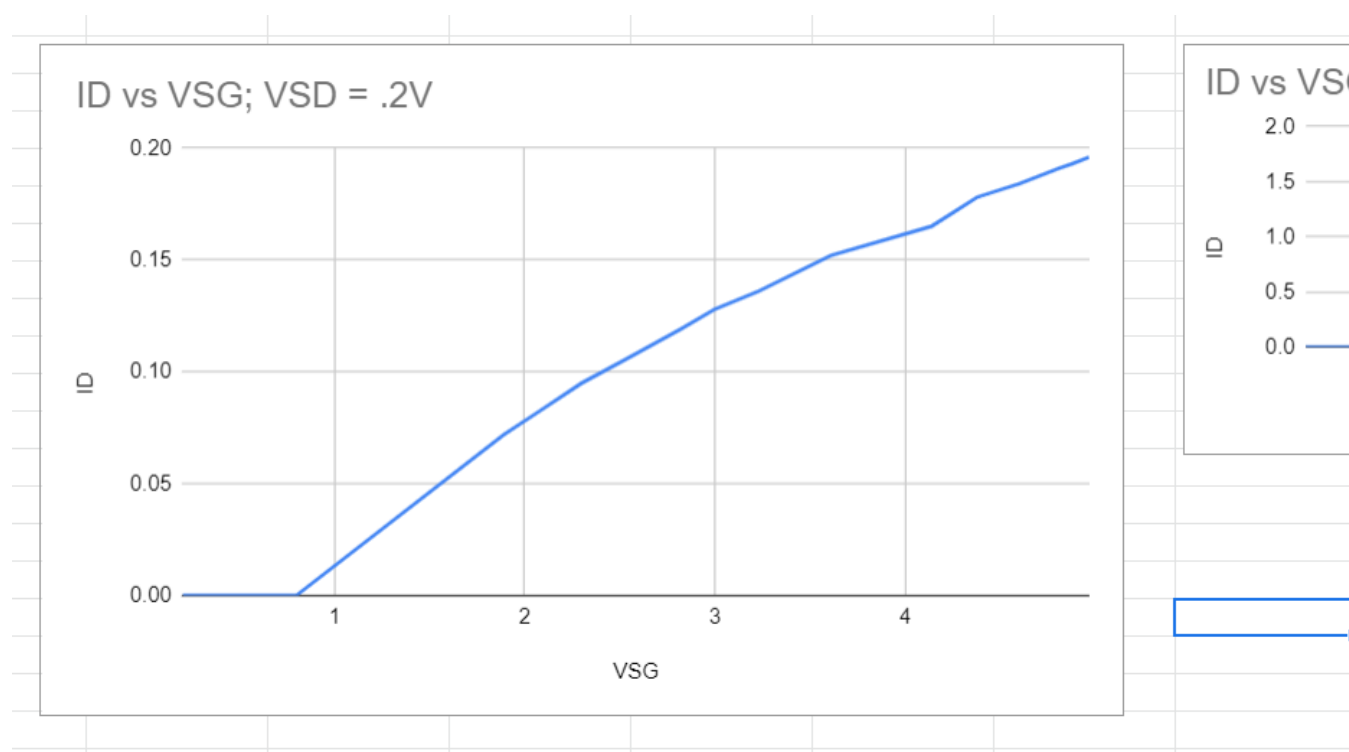


Figure 3: ID vs VSG

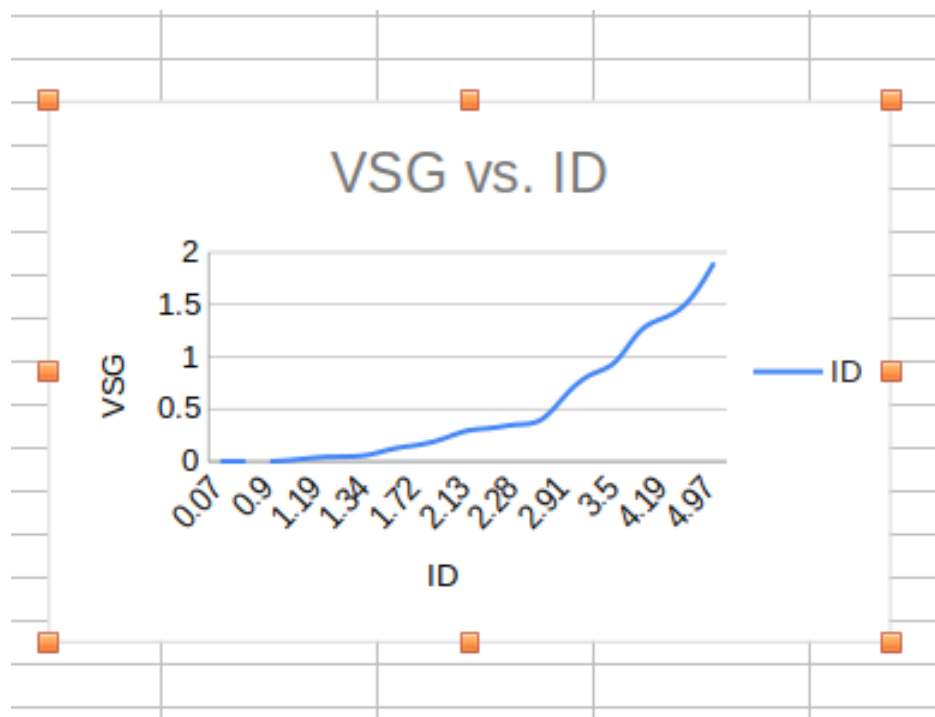


Figure 4: Vsd vs Id

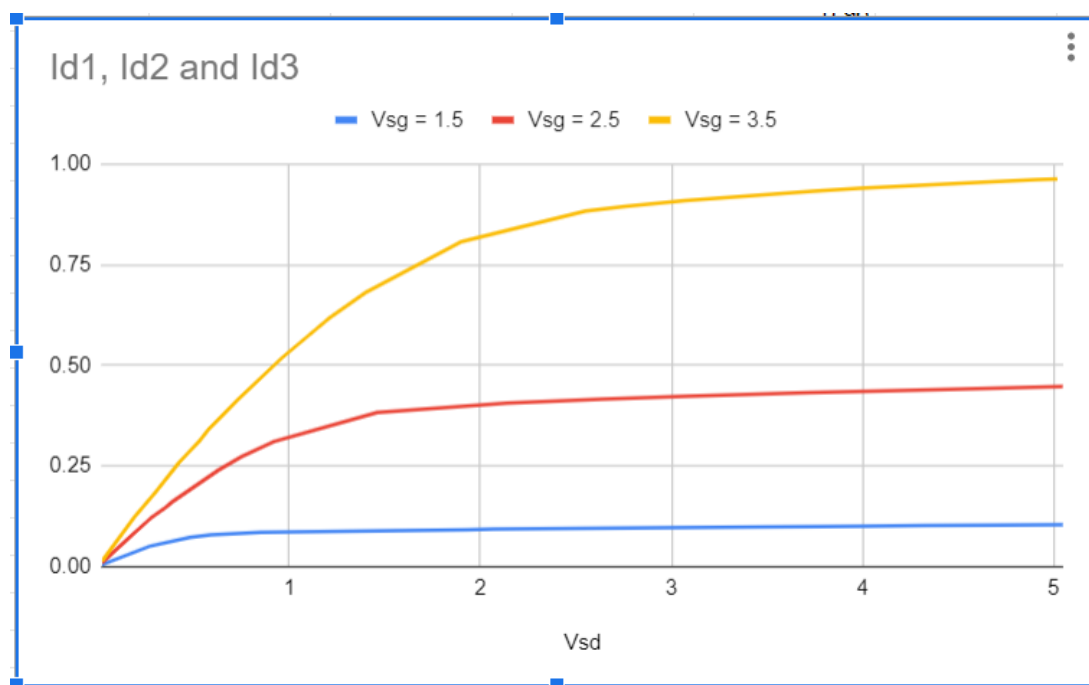


Figure 5: part2

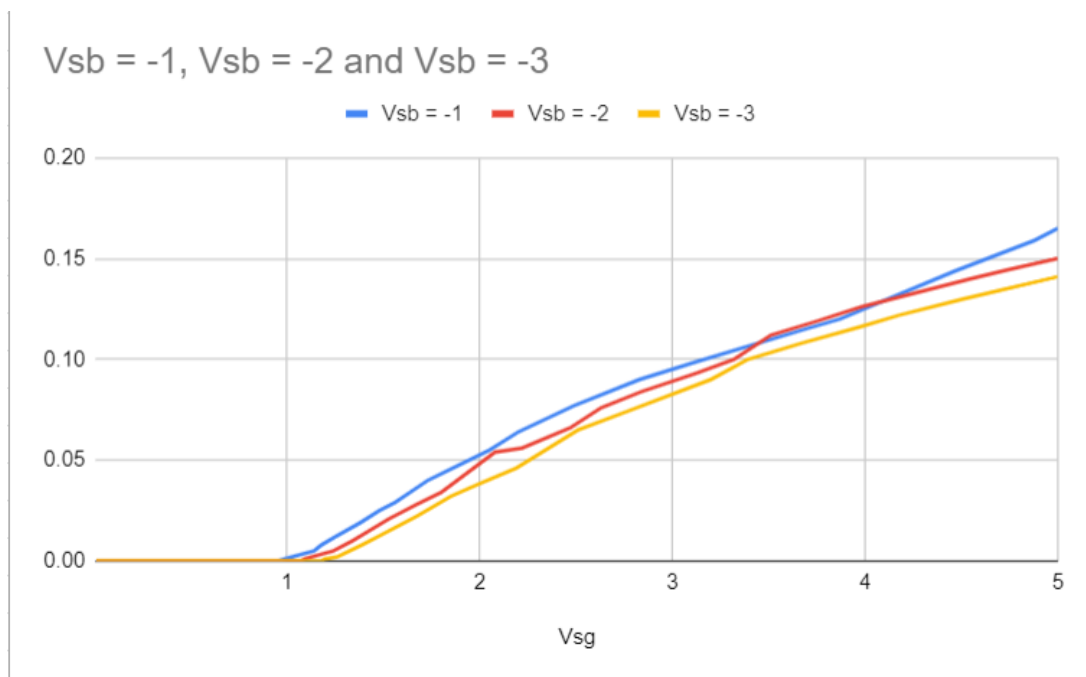


Figure 6: Part 3 - I_D vs V_{SG}

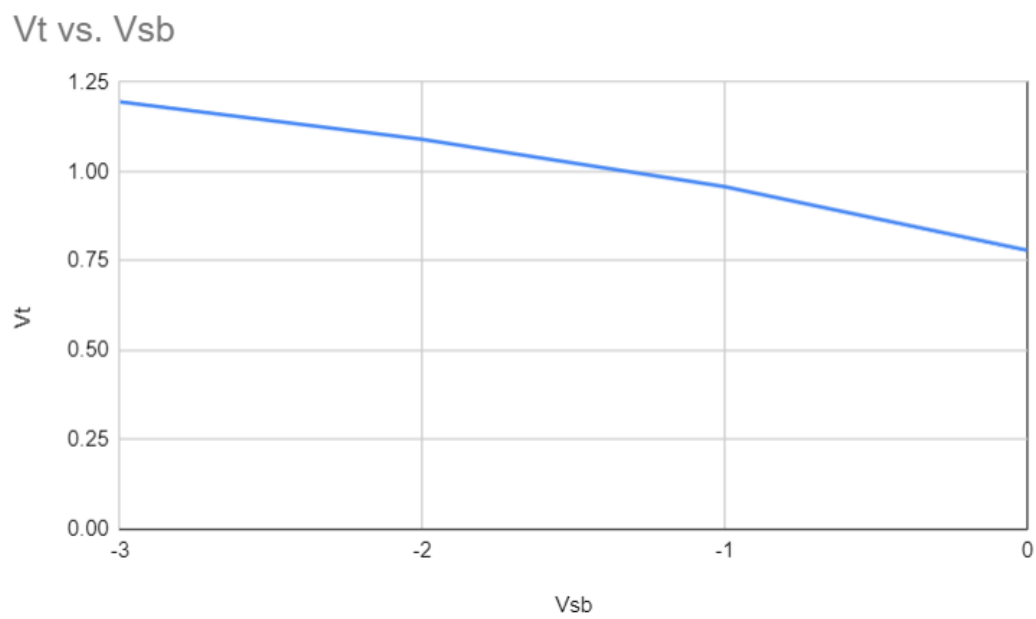


Figure 7: Part 3 - V_t vs V_{sb}